

NTE2507 Silicon NPN Transistor High Frequency Video Output

Absolute Maximum Ratings: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Collector-Base Voltage, V_{CB0}	200V
Collector-Emitter Voltage, V_{CEO}	200V
Emitter-Base Voltage, V_{EBO}	5V
Collector Current, I_C	400mA
Collector Power Dissipation ($T_C = +25^\circ\text{C}$), P_C	20W
Operating Junction Temperature, T_J	+150°C

Electrical Characteristics: ($T_A = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 150V$	-	-	0.1	μA
DC Current Gain	h_{FE}	$V_{CE} = 10V, I_C = 50\text{mA}$	40	-	320	
Transition Frequency	f_T	$V_{CE} = 30V, I_C = 100\text{mA}$	-	400	-	MHz
Output Capacitance	C_{ob}		-	4.2	-	pF

